SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

For low current rectification

Features

- High reliability
- Low reverse current





SOT-323 Plastic Package Marking Code: **ZA**

Absolute Maximum Ratings ($T_a = 25$ °C)

Parameter	Symbol	Value	Unit	
Repetitive Peak Reverse Voltage	V_{RM}	45	V	
Reverse Voltage	V_R	40	V	
Average Rectified Forward Current	Io	30	mA	
Peak Forward Surge Current (t = 8.3 ms)	I _{FSM}	200	mA	
Junction Temperature	T _j	125	°C	
Storage Temperature Range	T _{stg}	- 55 to + 125	°C	

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Тур.	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$	V_{F}	-	-	0.37	V
Reverse Current at V _R = 10 V	I _R	-	-	1	μΑ
Reverse Breakdown Voltage at I _R = 10 μA	$V_{(BR)R}$	45	-	-	V
Capacitance between Terminals at $V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$	Ст	-	2	-	pF



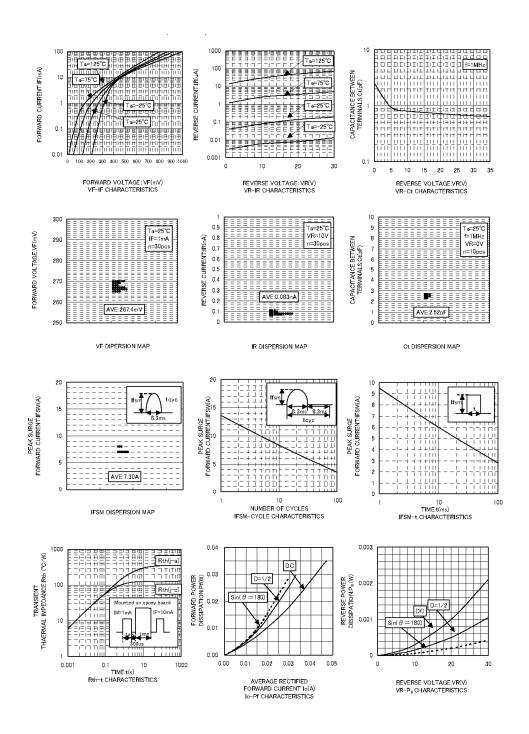








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SEMTECH ELECTRONICS LTD.

